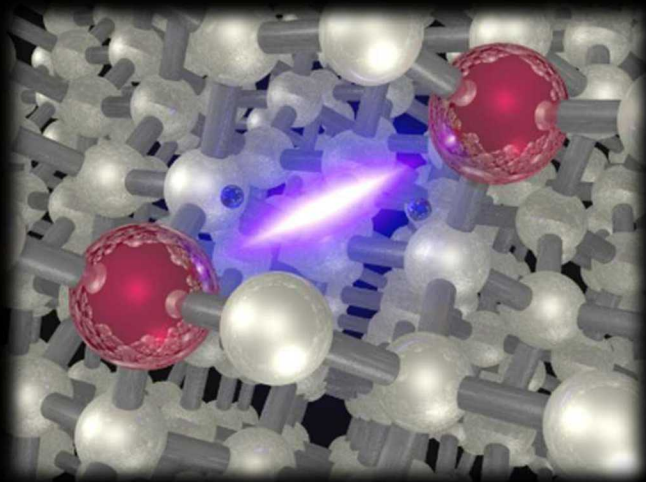


This paper describes objective technical results and analysis. Any subjective views or opinions that might be expressed in the paper do not necessarily represent the views of the U.S. Department of Energy or the United States Government.

Full configuration interaction simulations of exchange coupled donors in silicon in an effective mass theory framework

SAND2020-2632C



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QUANTUM COMPUTATION
COMMUNICATION TECHNOLOGY



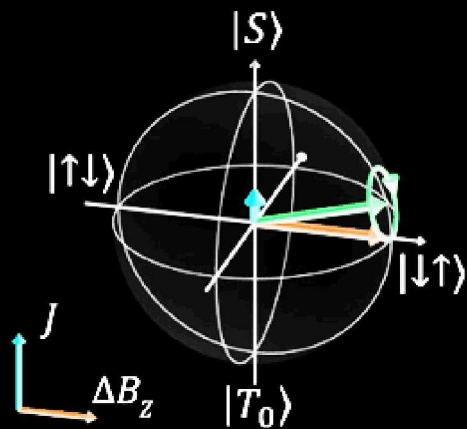
Australian Government

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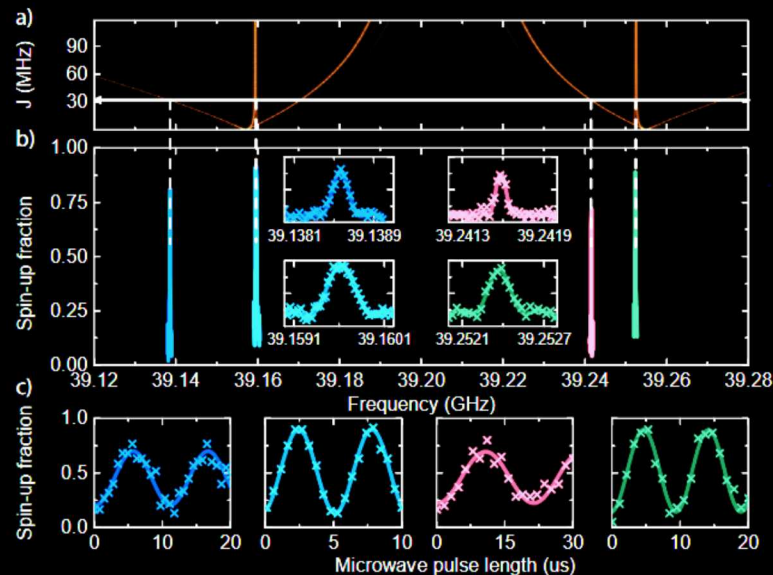


Two-Qubit Gates in Silicon

1. Weak exchange and ESR pulses



Donors

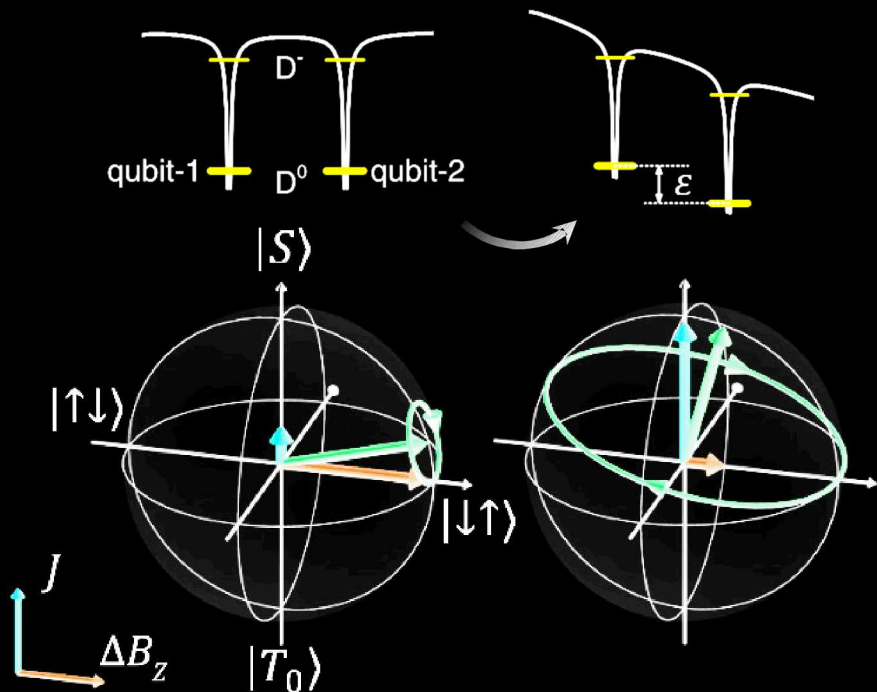


Madzik M., et al. in preparation

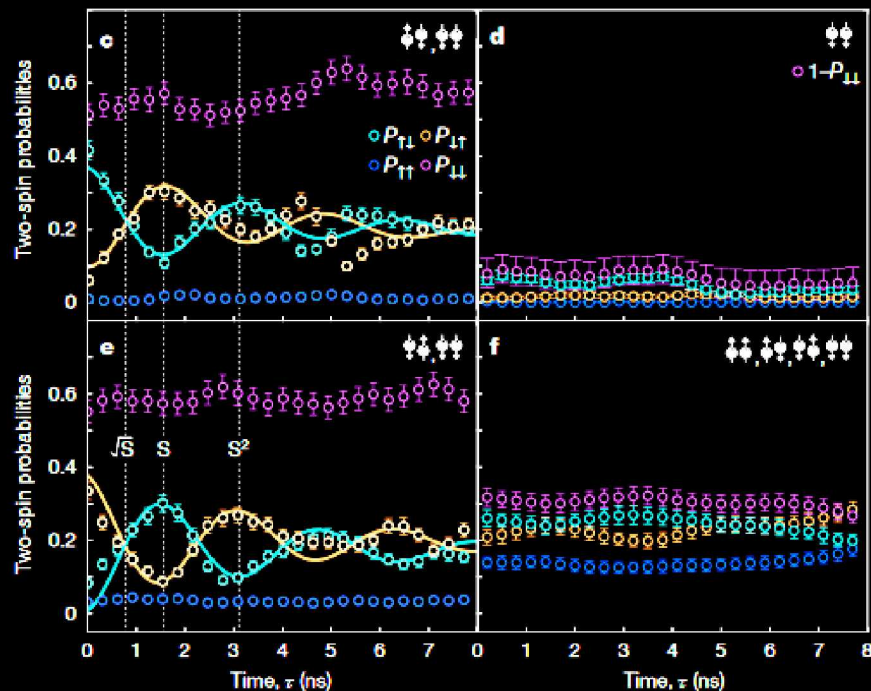


Two-Qubit Gates in Silicon

2. Strongly tuneable exchange



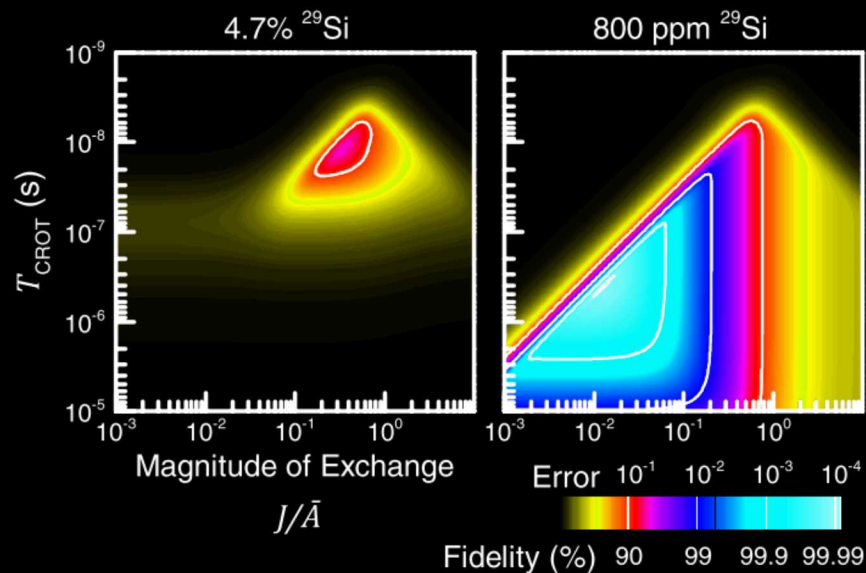
SWAP oscillations:



He Y. et al. *Nature* 571.7765 (2019): 371-375.

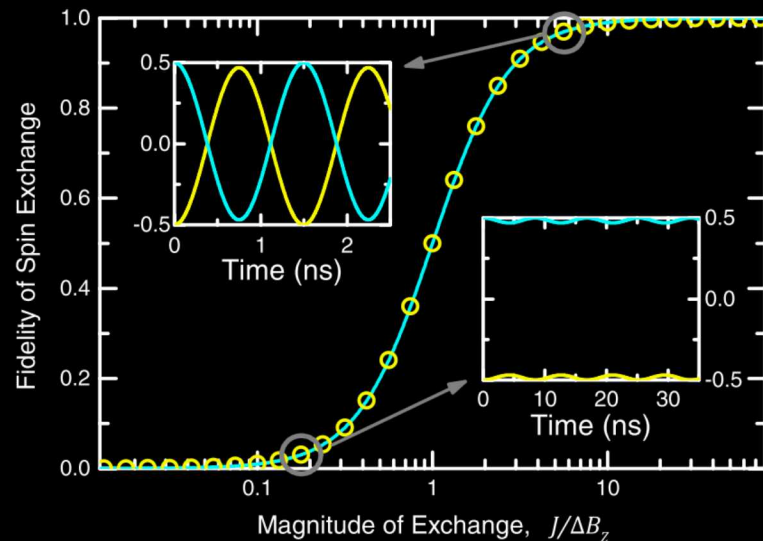
Requirements for High Fidelity

1. Weak exchange and ESR pulses



$$J < \frac{A}{10} = 11.7 \text{ MHz}$$

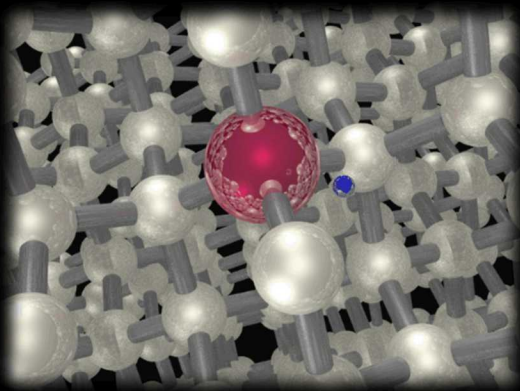
2. Strongly tuneable exchange



For high Fidelity:

$J \sim 10 \text{ MHz}$ $\longleftrightarrow$ Tuneable $\longleftrightarrow$ $J \sim 1 \text{ GHz}$

Multivalley Effective Mass Theory

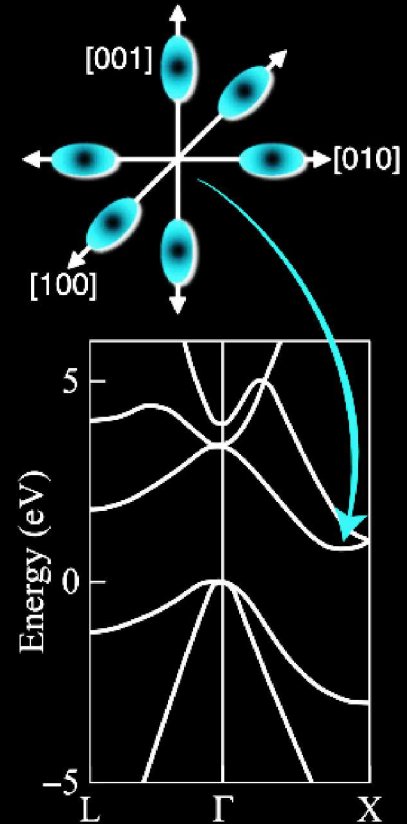
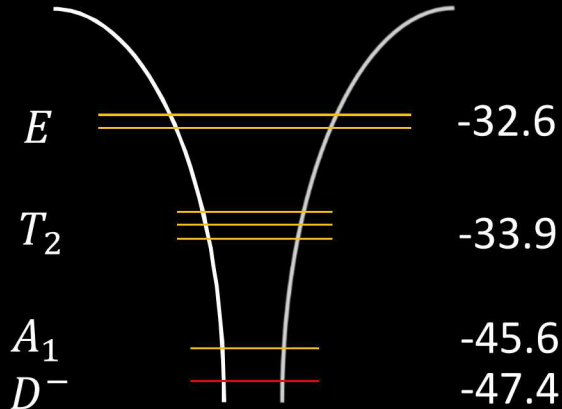


Ansatz:

$$\psi(\vec{r}) = \sum_{j=1}^6 F_j(\vec{r}) \phi_j(\vec{r})$$

Ingredients:

- Effective donor potential
 $U(\vec{r}) \propto 1/r$
- Anisotropic effective mass
 $m_{\parallel} \quad m_{\perp}$
- Valley orbit coupling
 $V_{i,j}^{VO}(\vec{r}) = \langle \phi_i | U(\vec{r}) | \phi_j \rangle$



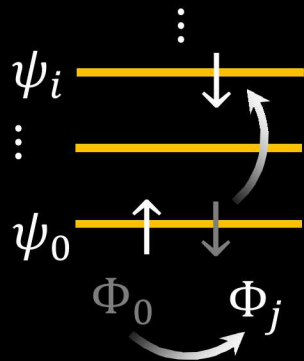
Gamble J.K. et al. *Physical Review B* 91.23 (2015): 235318.

Configuration Interaction

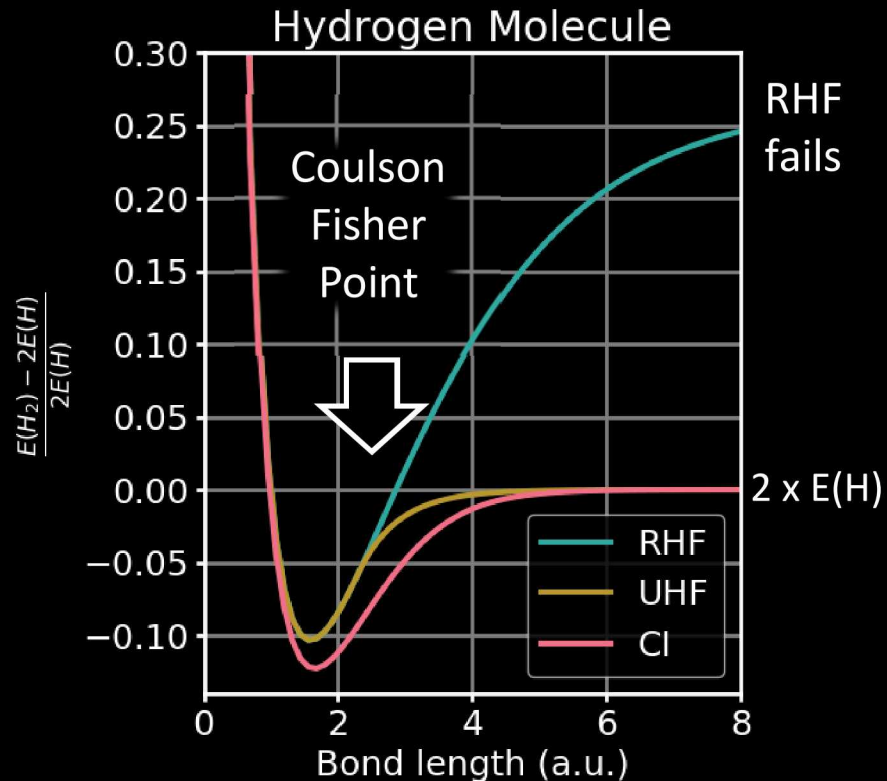
Hartree-Fock Approximation:

$$\Phi = \frac{1}{\sqrt{2}} (|\psi_i \psi_j\rangle |\uparrow \downarrow\rangle - |\psi_j \psi_i\rangle |\downarrow \uparrow\rangle)$$

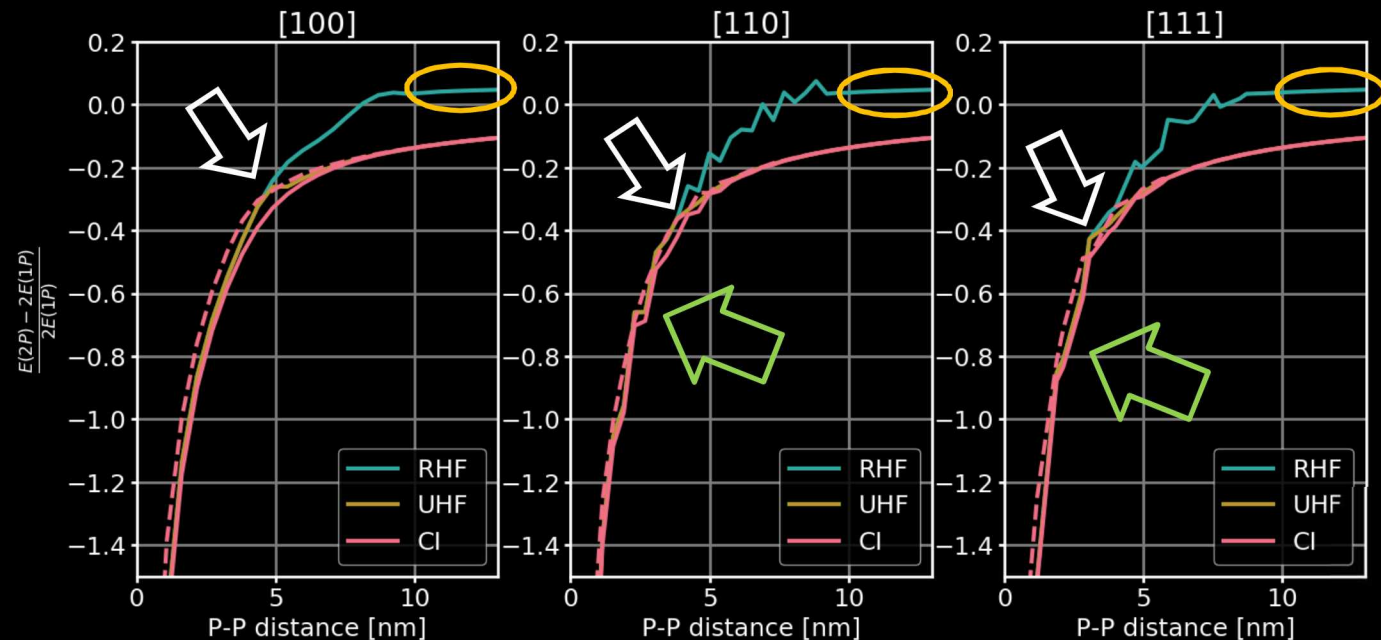
Configuration Interaction:



$$\Psi = \sum_i a_i \Phi_i$$



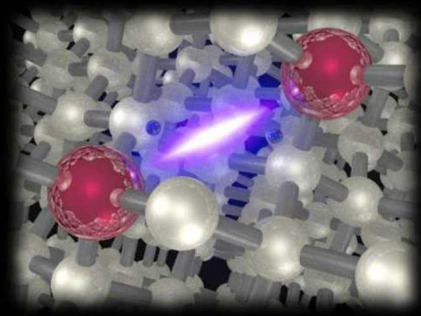
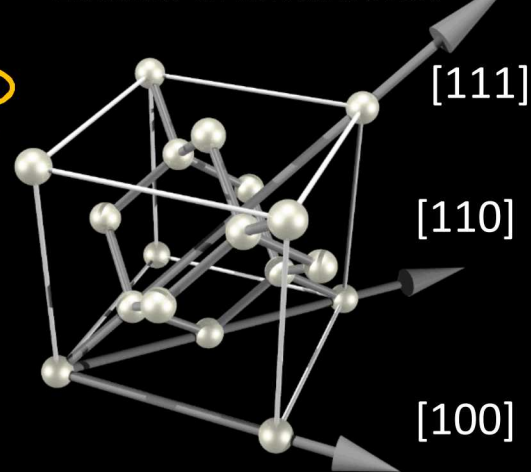
Phosphorus Donor Molecule



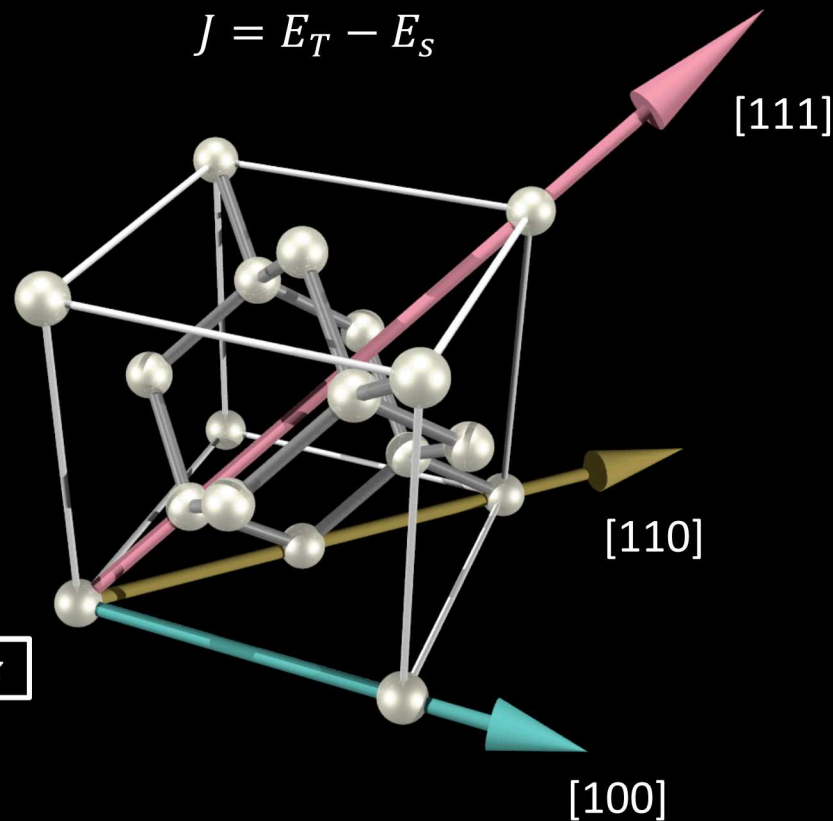
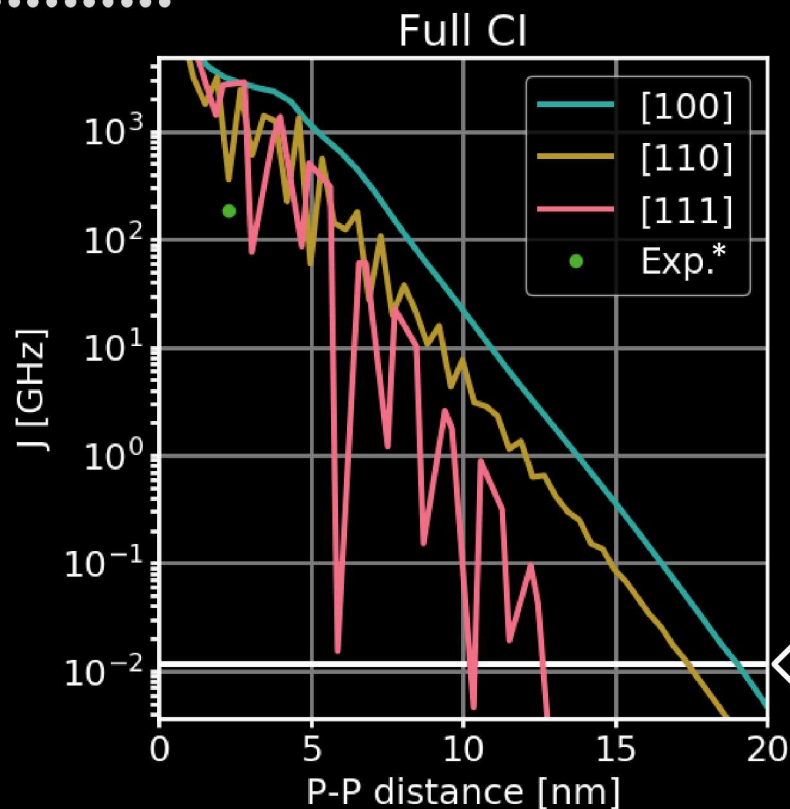
RHF fails for large distances

Valley oscillations along [110] and [111]

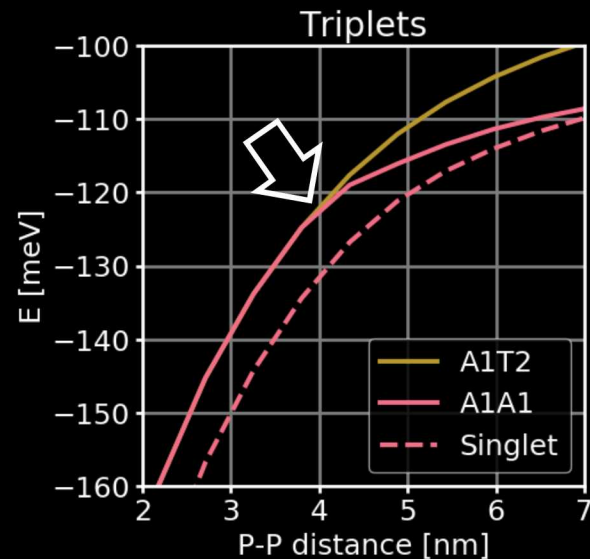
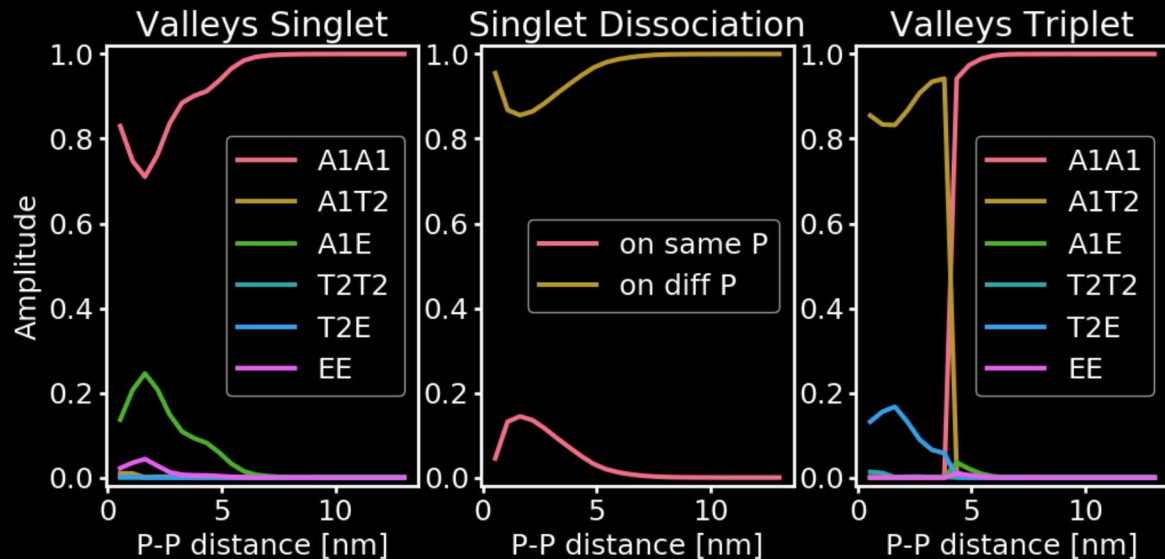
Lattice orientations:



Exchange Interaction



Valley Configuration [100]

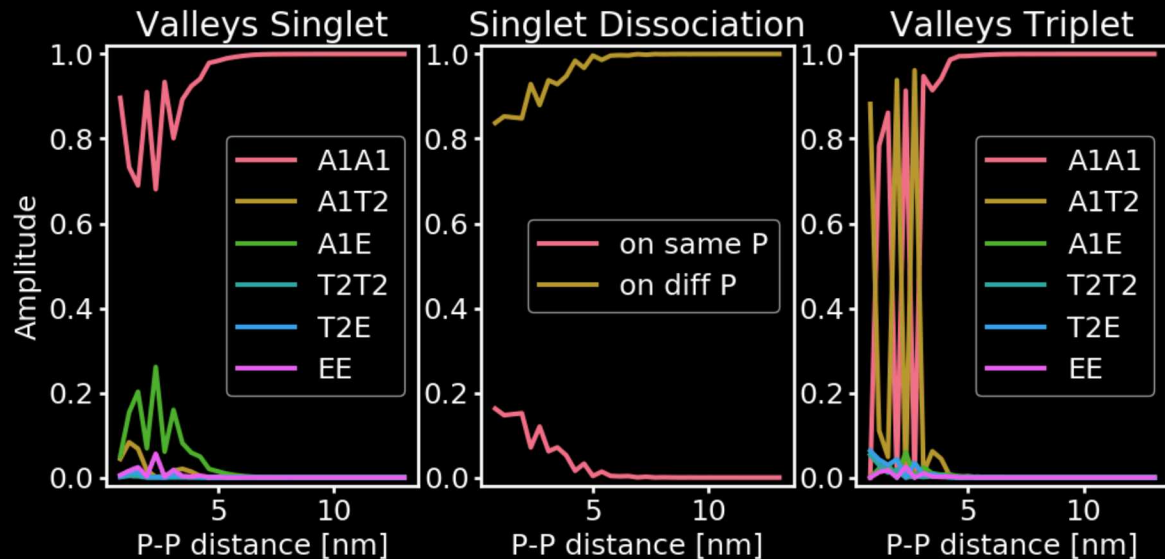


Anticrossing with first excited triplet.

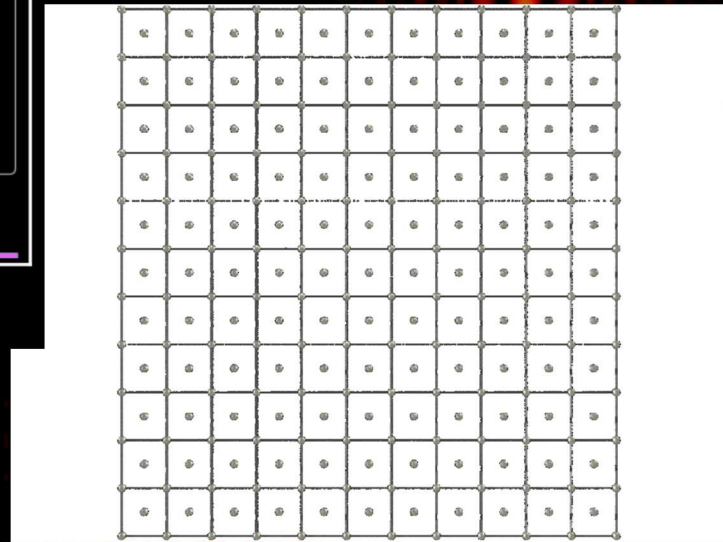
Dehollain, Juan P., et al. *Physical review letters* 112.23 (2014): 236801.



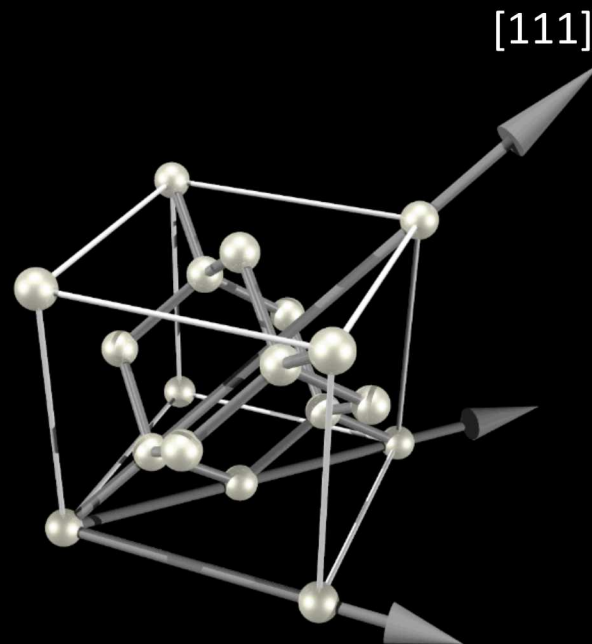
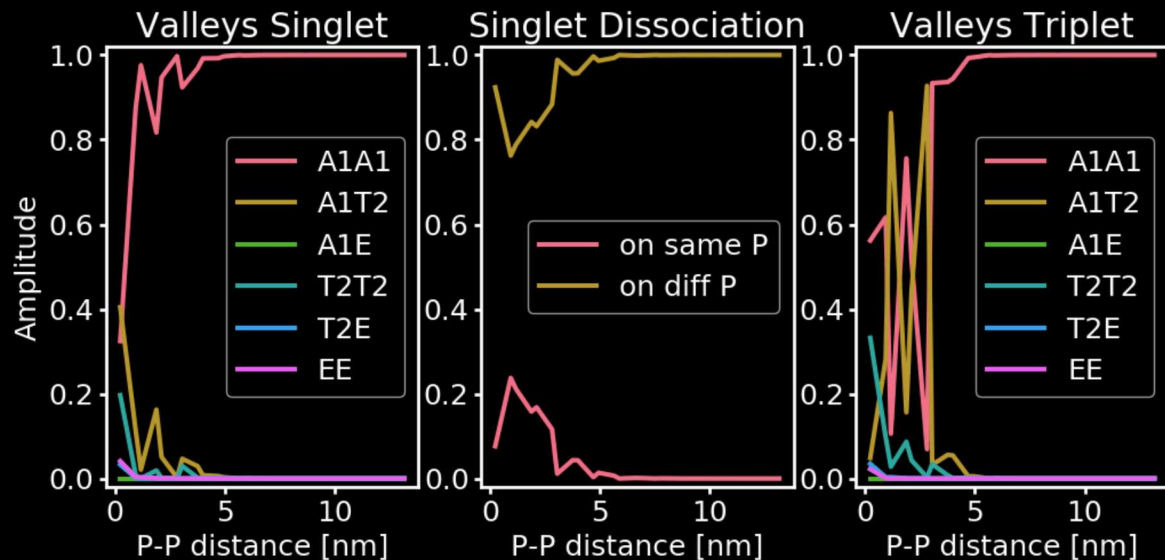
Valley Oscillations along [110]



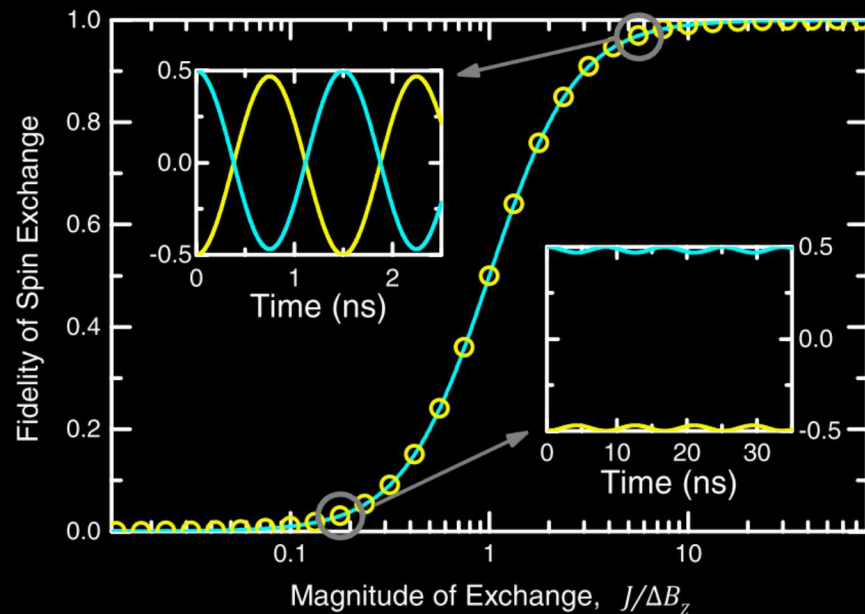
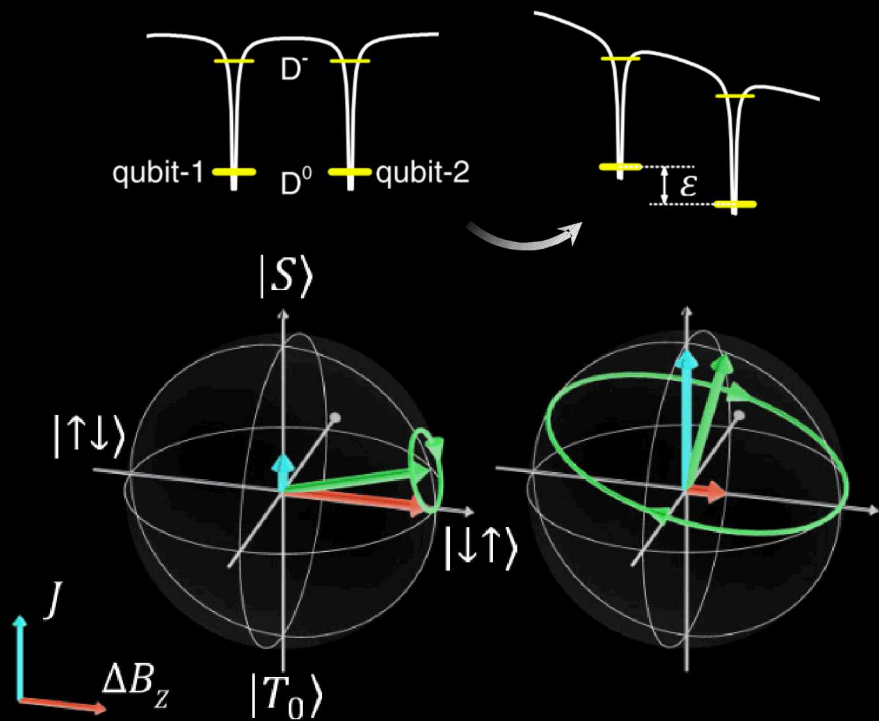
Strength of state overlap
oscillates



Valley Oscillations along [111]



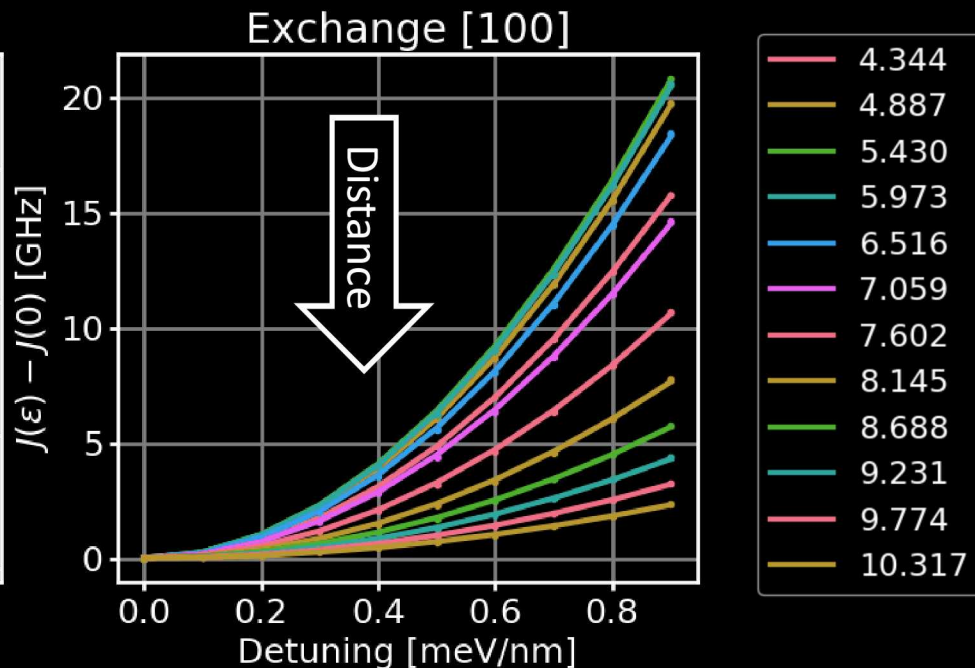
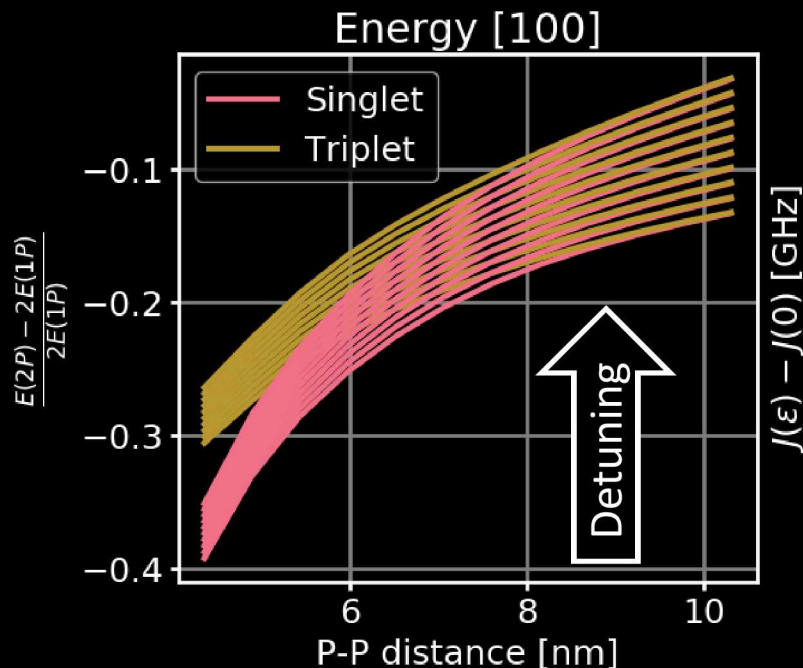
Electric Tunability for SWAP Gates



For high Fidelity:

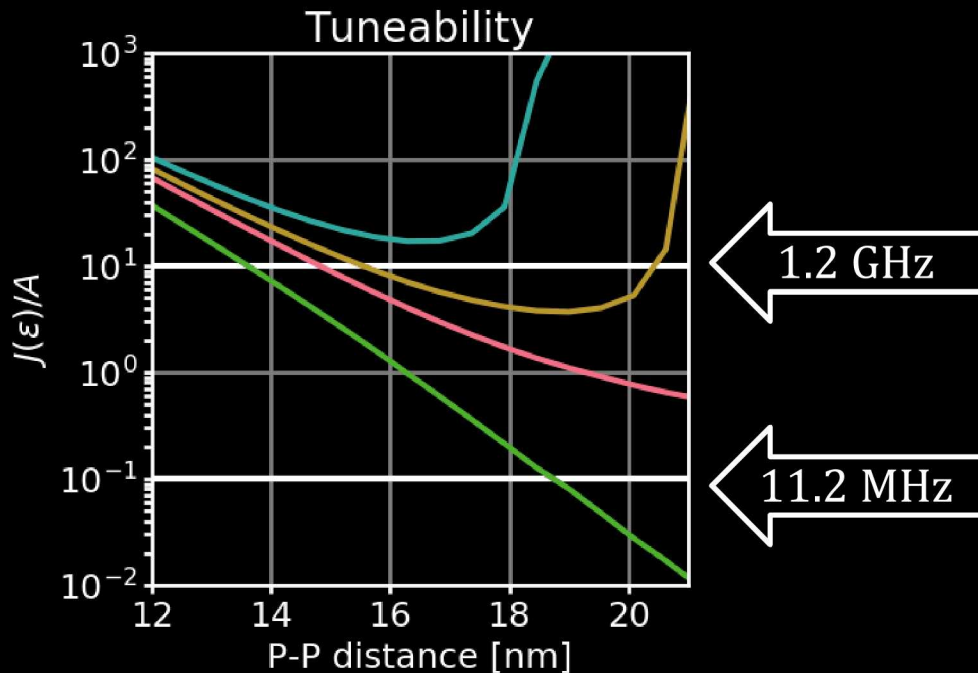
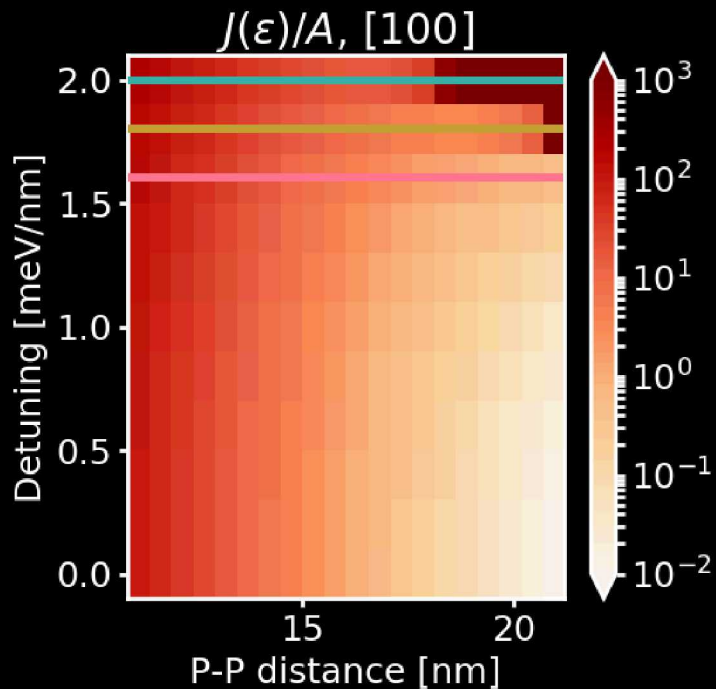
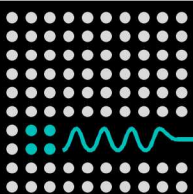
$J \sim 10\text{MHz}$ $\longleftrightarrow$ Tuneable $\longleftrightarrow$ $J \sim 1\text{GHz}$

Exchange Tunability



Quadratic growth

Implementing a SWAP Gate



$$d_{[100]} = 20.63 \text{ nm}$$
$$\Delta\epsilon = 1.8 \text{ meV/nm}$$



Highlights

